

Richard A Hogg

List of Publications by Year in descending order

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278
papers

3,660
citations

186265

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51
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281
all docs

281
docs citations

281
times ranked

2298
citing authors

#	ARTICLE	IF	CITATIONS
1	PL and PLE characterization of high current density resonant tunnelling diodes for THz applications. , 2022, , .		0
2	Cu2O-Based Electrochemical Biosensor for Non-Invasive and Portable Glucose Detection. Biosensors, 2022, 12, 174.	4.7	20
3	Increase in terahertz-wave intensity in a magnetic field due to difference-frequency mixing by exciton excitation in a GaAs/AlAs multiple quantum well. Optics Express, 2022, 30, 11789.	3.4	2
4	Near-infrared dual-wavelength surface-emitting light source using InAs quantum dots resonant with vertical cavity modes. Japanese Journal of Applied Physics, 2022, 61, SD1003.	1.5	0
5	Polarization-pinning in substrate emission multi-mode vertical-cavity surface-emitting lasers using deep trenches. Applied Physics Letters, 2022, 120, 211102.	3.3	1
6	1.1 μm waveband tunable laser using emission-wavelength-controlled InAs quantum dots for swept-source optical coherence tomography applications. Japanese Journal of Applied Physics, 2021, 60, SBBE02.	1.5	3
7	Photoluminescence excitation spectroscopy for structural and electronic characterization of resonant tunneling diodes for THz applications. AIP Advances, 2021, 11, 035122.	1.3	3
8	Fitting of photoluminescence spectra for structural characterisation of high current density resonant tunnelling diodes for THz applications. , 2021, , .		3
9	Emission wavelength control of InAs/GaAs quantum dots using an As ₂ source for near-infrared broadband light source applications. Applied Physics Express, 2021, 14, 055501.	2.4	1
10	Comparative analysis of void-containing and all-semiconductor 1.5 μm InP-based photonic crystal surface-emitting laser diodes. AIP Advances, 2021, 11, .	1.3	5
11	Modulation of exciton states through resonant excitation by continuous wave lasers in a GaAs/AlAs multiple quantum well. Journal Physics D: Applied Physics, 2021, 54, 335106.	2.8	1
12	Increase in terahertz-wave generation by difference frequency mixing by the overlap of exciton states in different GaAs/AlAs quantum wells and spectroscopic measurements. Optics Express, 2021, 29, 24387.	3.4	4
13	Micro-photoluminescence characterisation of structural disorder in resonant tunneling diodes for THz applications. , 2021, , .		1
14	Micro-PL analysis of high current density resonant tunneling diodes for THz applications. Applied Physics Letters, 2021, 119, 072102.	3.3	1
15	Void engineering in epitaxially regrown GaAs-based photonic crystal surface emitting lasers by grating profile design. Applied Physics Letters, 2021, 118, .	3.3	11
16	Coherent power scaling in photonic crystal surface emitting laser arrays. AIP Advances, 2021, 11, .	1.3	9
17	Monolithic All-Semiconductor PCSEs emitting at 1.3 μm . , 2021, , .		1
18	Bandwidth enhancement in an InGaN/GaN three-section superluminescent diode for optical coherence tomography. Applied Physics Letters, 2020, 117, .	3.3	3

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19	Resonant exciton excitation photoluminescence and dynamics in a GaAs/AlAs multiple quantum well with internal electric field. AIP Advances, 2020, 10, .	1.3	8
20	1.5 μ m Epitaxially Regrown Photonic Crystal Surface Emitting Laser Diode. IEEE Photonics Technology Letters, 2020, 32, 1531-1534.	2.5	17
21	Azimuthally Apodized Focusing Gratings. , 2020, , .		0
22	Broadband THz absorption spectrometer based on excitonic nonlinear optical effects. Light: Science and Applications, 2019, 8, 29.	16.6	11
23	Development of a broadband superluminescent diode based on self-assembled InAs quantum dots and demonstration of high-axial-resolution optical coherence tomography imaging. Journal Physics D: Applied Physics, 2019, 52, 225105.	2.8	15
24	Discontinuities in Multilayer Waveguides to Mode-2-D Photonic Crystal Structures. , 2019, , .		1
25	Modeling and Device Simulation of Photonic Crystal Surface Emitting Lasers Based on Modal Index Analysis. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-9.	2.9	13
26	Non-destructive characterization of thin layer resonant tunneling diodes. Journal of Applied Physics, 2019, 126, .	2.5	4
27	Proposal for Common Active 1.3- μ m Quantum Dot Electroabsorption Modulated DFB Laser. IEEE Photonics Technology Letters, 2019, 31, 419-422.	2.5	5
28	Evaluating resonances in PCSEL structures based on modal indices. IET Optoelectronics, 2019, 13, 17-22.	3.3	4
29	Tunable external cavity laser diode based on wavelength controlled self-assembled InAs quantum dots for swept-source optical coherence tomography applications at 1100 nm wavelength band. , 2019, , .		5
30	Characterisation of thin-layer resonant tunnelling diodes grown by MOVPE. , 2019, , .		3
31	Development of All-Semiconductor Photonic Crystal Surface Emitting Lasers. , 2019, , .		0
32	Resilience of state-of-the-art 1300nm In(Ga)As/GaAs quantum-dot lasers to external optical feedback (Withdrawal Notice). , 2019, , .		0
33	Epitaxial Designs for Maximizing Efficiency in Resonant Tunneling Diode Based Terahertz Emitters. IEEE Journal of Quantum Electronics, 2018, 54, 1-11.	1.9	13
34	Near-infrared and mid-infrared semiconductor broadband light emitters. Light: Science and Applications, 2018, 7, 17170-17170.	16.6	62
35	Resonant Tunnelling Diodes for next generation THz systems. , 2018, , .		1
36	Development of All-Semiconductor Photonic Crystal Surface Emitting Lasers. , 2018, , .		0

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37	Modal Index Analysis of Resonances of PCSEL , 2018, , .		0
38	Modelling and Device Simulation of Photonic Crystal Surface Emitting Lasers Based on Modal Index Analysis. , 2018, , .		0
39	In-Line Non-Destructive Characterisation Method for Photonic Crystal Surface Emitting Lasers. , 2018,		0
40	Wide Frequency Tuning of Continuous Terahertz Wave Generated by Difference Frequency Mixing under Exciton-Excitation Conditions in a GaAs Multiple Quantum Well. AlAs Size anisotropy inhomogeneity effects in state-of-the-art quantum dot lasers. Applied Physics Letters, 2018, 113, 012105.	3.8	6
41	Effect of rapid thermal annealing on threading dislocation density in III-V epilayers monolithically grown on silicon. Journal of Applied Physics, 2018, 123, .	2.5	12
42	Incorporating structural analysis in a quantum dot Monte-Carlo model. , 2018, , .		0
44	Growth of quantum three-dimensional structure of InGaAs emitting at $\sim 1 \mu\text{m}$ applicable for a broadband near-infrared light source. Journal of Crystal Growth, 2017, 477, 230-234.	1.5	6
45	Optimisation of photonic crystal coupling through waveguide design. Optical and Quantum Electronics, 2017, 49, 47.	3.3	12
46	Gallium nitride light sources for optical coherence tomography. , 2017, , .		9
47	Fabrication, characterisation, and epitaxial optimisation of MOVPE-grown resonant tunnelling diode THz emitters. , 2017, , .		2
48	Mode Control in Photonic Crystal Surface Emitting Lasers Through External Reflection. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-8.	2.9	8
49	Gallium Nitride Superluminescent Light Emitting Diodes for Optical Coherence Tomography Applications. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-11.	2.9	21
50	Strain Balancing of Metal-Organic Vapour Phase Epitaxy InAs/GaAs Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-8.	2.9	5
51	Room temperature tuneable THz generation based on 2nd order non-linear optical effects in GaAs/AlGaAs multi-quantum well excitons. , 2017, , .		0
52	Valley current characterization of high current density resonant tunnelling diodes for terahertz-wave applications. AIP Advances, 2017, 7, .	1.3	11
53	Mode control in photonic crystal surface emitting lasers (PCSELs) through in-plane feedback (Conference Presentation). , 2017, , .		0
54	High-speed high-sensitivity infrared spectroscopy using mid-infrared swept lasers (Conference)		

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55	GaAs-based superluminescent diodes with window-like facet structure for low spectral modulation at high output powers. Semiconductor Science and Technology, 2016, 31, 045003.	2.0	4
56	Superluminescent diode with a broadband gain based on self-assembled InAs quantum dots and segmented contacts for an optical coherence tomography light source. Journal of Applied Physics, 2016, 119, 083107.	2.5	23
57	Epitaxial design for maximising wall plug efficiency in resonant tunnelling diode terahertz emitters. , 2016, , .		1
58	Characterisation of high current density resonant tunnelling diodes for THz emission using photoluminescence spectroscopy. , 2016, , .		1
59	10â€‰%â€‰GHz pulse repetition rate Er:Yb:glass laser modelocked with quantum dot semiconductor saturable absorber mirror. Applied Optics, 2016, 55, 3776.	2.1	12
60	Photoluminescence Characterisation of High Current Density Resonant Tunnelling Diodes for Terahertz Applications. IEICE Transactions on Electronics, 2016, E99.C, 181-188.	0.6	5
61	Photonic crystal surface emitting lasers â€” Coherent arrays and external feedback. , 2016, , .		0
62	Dominant role of many-body effects on the carrier distribution function of quantum dot lasers. Applied Physics Express, 2016, 9, 032705.	2.4	5
63	High input resistance terahertz dipole antenna with an isolating photonic band gap layer. , 2016, , .		3
64	Rigorous comparison of the spectral SNR of FTIR and EC-QCL spectroscopy (Conference Presentation). , 2016, , .		0
65	GaAs-based self-aligned stripe superluminescent diodes processed normal to the cleaved facet. Proceedings of SPIE, 2016, , .	0.8	0
66	Characterisation of high current density resonant tunneling diodes for THz emission using photoluminescence spectroscopy. Proceedings of SPIE, 2016, , .	0.8	4
67	Three-dimensional finite-difference time-domain modelling of photonic crystal surface-emitting lasers. , 2016, , .		1
68	Optimization of the epitaxial design of high current density resonant tunneling diodes for terahertz emitters. , 2016, , .		1
69	Simulation of broad spectral bandwidth emitters at 1060 nm for optical coherence tomography. , 2016, , .		0
70	Study of electro-absorption effects in 1300nm In(Ga)As/GaAs quantum dot materials. Proceedings of SPIE, 2016, , .	0.8	2
71	Electrically Driven Near-Infrared Broadband Light Source with Gaussian-Like Spectral Shape Based on Multiple InAs Quantum Dots. IEICE Transactions on Electronics, 2016, E99.C, 381-384.	0.6	8
72	Imaging of spectral-domain optical coherence tomography using a superluminescent diode based on InAs quantum dots emitting broadband spectrum with Gaussian-like shape. Japanese Journal of Applied Physics, 2015, 54, 04DG07.	1.5	16

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73	Optimization of high current density resonant tunneling diodes for terahertz emitters. , 2015, , .		1
74	Lasers and SLEDs for optical coherence tomography. , 2015, , .		0
75	3D FDTD modelling of photonic crystal surface emitting lasers. , 2015, , .		1
76	Electronic control of coherence in a two-dimensional array of photonic crystal surface emitting lasers. Scientific Reports, 2015, 5, 13203.	3.3	23
77	Substrate removal and capillary bonding of a quantum beat sample. , 2015, , .		0
78	Monte Carlo model incorporating many-body effects for determining the gain spectra of quantum dot lasers. Applied Physics Express, 2015, 8, 122102.	2.4	3
79	A PHOTOMIXER DRIVEN TERAHERTZ DIPOLE ANTENNA WITH HIGH INPUT RESISTANCE AND GAIN. Progress in Electromagnetics Research M, 2015, 44, 13-20.	0.9	5
80	Coherently Coupled Photonic-Crystal Surface-Emitting Laser Array. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 493-499.	2.9	16
81	Radiation tolerant DC characteristics of InAs/GaAs quantum-dot diodes. , 2015, , .		1
82	Optimisation of fundamental transverse mode output in electrically pumped vertical external cavity surface emitting lasers. Proceedings of SPIE, 2015, , .	0.8	0
83	Platform manufacturing technique for next generation integrated photonic components. , 2015, , .		0
84	A Dual-Pass High Current Density Resonant Tunneling Diode for Terahertz Wave Applications. IEEE Electron Device Letters, 2015, 36, 1295-1298.	3.9	21
85	A dual-pass high current density resonant tunnelling diode terahertz emitter. , 2015, , .		2
86	Non-destructive mapping of doping and structural composition of MOVPE-grown high current density resonant tunnelling diodes through photoluminescence spectroscopy. Journal of Crystal Growth, 2015, 418, 102-110.	1.5	15
87	The mid-infrared swept laser: life beyond OCT?. , 2015, , .		0
88	Waveguide and photonic crystal design of photonic crystal surface-emitting laser. Proceedings of SPIE, 2015, , .	0.8	0
89	Sensitivity Advantage of QCL Tunable-Laser Mid-Infrared Spectroscopy Over FTIR Spectroscopy. Applied Spectroscopy Reviews, 2015, 50, 822-839.	6.7	46
90	Optical characterization of In-flushed InAs/GaAs quantum dots emitting a broadband spectrum with multiple peaks at $\sim 1 \frac{1}{4} \mu\text{m}$. Nanoscale Research Letters, 2015, 10, 231.	5.7	8

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91	Robust electrical characteristics of multiple-layer InAs/GaAs quantum-dot diodes under gamma irradiation. , 2015, , .		0
92	GaAs-Based Superluminescent Light-Emitting Diodes with 290-nm Emission Bandwidth by Using Hybrid Quantum Well/Quantum Dot Structures. Nanoscale Research Letters, 2015, 10, 1049.	5.7	21
93	Terahertz dipole antenna performance enhancement using a photonic-bandgap GaAs substrate. , 2014, , .		0
94	Gain spectrum measurement using the segmented contact method with an integrated optical amplifier. Journal of Applied Physics, 2014, 115, 163105.	2.5	3
95	Near- infrared, mode-locked waveguide lasers with multi-GHz repetition rates. , 2014, , .		0
96	Development of broad spectral bandwidth hybrid QW/QD structures from 1000-1400 nm. , 2014, , .		1
97	Integration of Emission-Wavelength-Controlled InAs Quantum Dots for Ultra-Broadband Near-Infrared Light Source. Nanomaterials and Nanotechnology, 2014, 4, 26.	3.0	18
98	Near-infrared superluminescent diode using stacked self-assembled InAs quantum dots with controlled emission wavelengths. Japanese Journal of Applied Physics, 2014, 53, 04EG10.	1.5	21
99	Photonic waveguide engineering using pulsed lasers — A novel approach for non-clean room fabrication!. , 2014, , .		0
100	Photonic crystal surface emitting lasers based on epitaxial regrowth. , 2013, , .		1
101	Broad bandwidth emission from hybrid QW/QD structures. , 2013, , .		1
102	Extending emission wavelength of InAs/GaAs quantum dots beyond 1.3 μ m by using quantum dot bi-layer for broadband light source. Journal of Crystal Growth, 2013, 378, 553-557.	1.5	11
103	All-Semiconductor Photonic Crystal Surface-Emitting Lasers Based on Epitaxial Regrowth. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 4900407-4900407.	2.9	21
104	Hybrid Quantum Well/Quantum Dot Structure for Broad Spectral Bandwidth Emitters. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1900209-1900209.	2.9	23
105	Band structure and waveguide modelling of epitaxially regrown photonic crystal surface-emitting lasers. Journal Physics D: Applied Physics, 2013, 46, 264005.	2.8	13
106	A diode-pumped 1.5 μ m waveguide laser mode-locked at 6.8 GHz by a quantum dot SESAM. Laser Physics Letters, 2013, 10, 105803.	1.4	23
107	Monolithically grown multi-color InAs quantum dots as a spectral-shape-controllable near-infrared broadband light source. Applied Physics Letters, 2013, 103, .	3.3	15
108	Absorption and single-pass gain measurements in bilayer quantum dot laser structure. , 2013, , .		0

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109	High Pulse Repetition Rate Lasers Modelocked with Quantum Dot SESAMs. , 2013, , .		0
110	Diode-pumped, 6.8 GHz, solid-state waveguide laser mode-locked at 1.5 μ m by a quantum-dot SESAM. , 2013, , .		0
111	Effect of modulation p-doping on the differential carrier lifetime of quantum dot lasers. Proceedings of SPIE, 2012, , .	0.8	0
112	Self-assembled quantum dot-based swept laser source for optical coherence tomography applications. , 2012, , .		0
113	Effect of Deposition Temperature on the Opto-Electronic Properties of Molecular Beam Epitaxy Grown InAs Quantum Dot Devices for Broadband Applications. Japanese Journal of Applied Physics, 2012, 51, 02BG09.	1.5	5
114	Quantum dot selective area intermixing for broadband light sources. Optics Express, 2012, 20, 26950.	3.4	26
115	Epitaxially Regrown GaAs-Based Photonic Crystal Surface-Emitting Laser. IEEE Photonics Technology Letters, 2012, 24, 966-968.	2.5	38
116	Optimisation of Coupling between Photonic Crystal and Active Elements in an Epitaxially Regrown GaAs Based Photonic Crystal Surface Emitting Laser. Japanese Journal of Applied Physics, 2012, 51, 02BG05.	1.5	6
117	Active glass waveguide amplifier on GaAs by UV-pulsed laser deposition and femtosecond laser inscription. Laser Physics Letters, 2012, 9, 329-339.	1.4	11
118	Optimization of Quantum-Dot Molecular Beam Epitaxy for Broad Spectral Bandwidth Devices. IEEE Photonics Journal, 2012, 4, 2066-2073.	2.0	10
119	Realization of a photonic crystal surface emitting laser through GaAs based regrowth. Proceedings of SPIE, 2012, , .	0.8	1
120	Hybrid quantum well/quantum dot structures for broad spectral bandwidth devices. Proceedings of SPIE, 2012, , .	0.8	1
121	10 GHz Pulse Repetition Rate ERGO Laser Modelocked by a 1550 nm InAs/GaAs Quantum-Dot SESAM. , 2012, , .		1
122	The effect of growth temperature of GaAs nucleation layer on InAs/GaAs quantum dots monolithically grown on Ge substrates. Applied Physics Letters, 2012, 100, .	3.3	34
123	Negative differential gain in 1.3 μ m quantum dot lasers: comparison of self-heating and free carrier effects. Proceedings of SPIE, 2012, , .	0.8	0
124	Room temperature simultaneous three-state lasing in hybrid quantum well/quantum dot laser. Electronics Letters, 2012, 48, 644.	1.0	12
125	Photonic crystal surface emitting lasers based on epitaxial regrowth. , 2012, , .		0
126	Characterization of recombination processes in quantum dot lasers using small signal modulation. , 2012, , .		0

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127	1.55 Åµm InAs/GaAs Quantum Dots and High Repetition Rate Quantum Dot SESAM Mode-locked Laser. Scientific Reports, 2012, 2, 477.	3.3	65
128	Hybrid quantum well/quantum dot active element for broad spectral bandwidth emitters and amplifiers. , 2012, , .		0
129	Ultra-broad spontaneous emission and modal gain spectrum from a hybrid quantum well/quantum dot laser structure. Applied Physics Letters, 2012, 100, .	3.3	23
130	Broadband Light Source Based on Four-Color Self-Assembled InAs Quantum Dot Ensembles Monolithically Grown in Selective Areas. IEICE Transactions on Electronics, 2012, E95-C, 247-250.	0.6	6
131	Optimisation of Coupling between Photonic Crystal and Active Elements in an Epitaxially Regrown GaAs Based Photonic Crystal Surface Emitting Laser. Japanese Journal of Applied Physics, 2012, 51, 02BG05.	1.5	7
132	Effect of Deposition Temperature on the Opto-Electronic Properties of Molecular Beam Epitaxy Grown InAs Quantum Dot Devices for Broadband Applications. Japanese Journal of Applied Physics, 2012, 51, 02BG09.	1.5	9
133	Post-Growth Intermixing of GaAs Based Quantum Dot Devices. , 2012, , 109-130.		1
134	High Repetition Rate Ti:Sapphire Laser Mode-Locked by InP Quantum-Dot Saturable Absorber. IEEE Photonics Technology Letters, 2011, 23, 1603-1605.	2.5	10
135	Common path Michelson interferometer based on multiple reflections within the sample arm: sensor applications and imaging artefacts. Measurement Science and Technology, 2011, 22, 027002.	2.6	8
136	Swept-Source Laser Based on Quantum-Dot Semiconductor Optical Amplifier Applications in Optical Coherence Tomography. IEEE Photonics Technology Letters, 2011, 23, 739-741.	2.5	13
137	Long-wavelength InAs/GaAs quantum-dot laser diode monolithically grown on Ge substrate. Nature Photonics, 2011, 5, 416-419.	31.4	344
138	Common path FDOCT based on multiple reflections within the sample arm. Proceedings of SPIE, 2011, , .	0.8	0
139	Design and characterization of electrically pumped vertical external cavity surface emitting lasers. Proceedings of SPIE, 2011, , .	0.8	0
140	Evaluation of a swept-laser optical coherence tomography light source based on a novel quantum-dot based semiconductor optical amplifier. Proceedings of SPIE, 2011, , .	0.8	0
141	Gain and absorption characteristics of bilayer quantum dot lasers beyond 1.3 Åµm. Proceedings of SPIE, 2011, , .	0.8	1
142	Comparison of gain measurement techniques for 1.3 Åµm quantum dot lasers. Proceedings of SPIE, 2011, , .	0.8	1
143	Strain engineered bilayers for extending the operating wavelength of quantum dot lasers. IET Optoelectronics, 2011, 5, 100-104.	3.3	3
144	Toward 1550-nm GaAs-Based Lasers Using InAs/GaAs Quantum Dot Bilayers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1334-1342.	2.9	16

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145	Tradeoffs in the Realization of Electrically Pumped Vertical External Cavity Surface Emitting Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1745-1752.	2.9	11
146	Simulations of nanograting-assisted light coupling in GaN planar waveguide. Optical and Quantum Electronics, 2011, 42, 619-629.	3.3	6
147	Common path Fourier domain optical coherence tomography based on multiple reflections within the sample arm. Optics Communications, 2011, 284, 3168-3172.	2.1	6
148	Multi-color quantum dot ensembles grown in selective-areas for shape-controlled broadband light source. Journal of Crystal Growth, 2011, 323, 191-193.	1.5	10
149	Excited State Bilayer Quantum Dot Lasers at 1.3 Åµm. Japanese Journal of Applied Physics, 2011, 50, 04DG10.	1.5	1
150	Negative differential gain due to many body effects in self-assembled quantum dot lasers. Applied Physics Letters, 2011, 99, 061104.	3.3	15
151	Subthreshold diode characteristics of InAs/GaAs quantum dot lasers. Physical Review B, 2011, 83, .	3.2	5
152	Erbium doped glass-semiconductor integrated waveguide amplifier. , 2011, , .		0
153	O-band excited state quantum dot bilayer lasers. Applied Physics Letters, 2011, 99, 051101.	3.3	11
154	Epitaxially regrown gaas based photonic crystal surface emitting laser. , 2011, , .		0
155	Design Rules and Characterisation of Electrically Pumped Vertical External Cavity Surface Emitting Lasers. Japanese Journal of Applied Physics, 2011, 50, 04DG05.	1.5	3
156	1.52Åµm electroluminescence from GaAs-based quantum dot bilayers. Electronics Letters, 2011, 47, 44.	1.0	4
157	Excited State Bilayer Quantum Dot Lasers at 1.3 Åµm. Japanese Journal of Applied Physics, 2011, 50, 04DG10.	1.5	1
158	Evaluation of a swept-laser optical coherence tomography light source based on a novel quantum-dot based semiconductor optical amplifier. , 2011, , .		0
159	Dual-state lasing and the case against the phonon bottleneck. , 2010, , .		1
160	Study of the effect of annealing of In(Ga)As quantum dots. Journal of Physics: Conference Series, 2010, 241, 012054.	0.4	2
161	Bilayer for extending the wavelength of QD lasers. Journal of Physics: Conference Series, 2010, 245, 012083.	0.4	4
162	Temperature dependence of Ga-assisted oxide desorption on GaAs(001). Journal of Physics: Conference Series, 2010, 209, 012066.	0.4	7

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163	A platform for GaAs opto-electronic integrated circuits based on GaAs/AlGaAs regrowth upon patterned InGaP. , 2010, , .		0
164	Ga assisted oxide desorption on GaAs(001) studied by scanning tunnelling microscopy. Journal of Crystal Growth, 2010, 312, 1687-1692.	1.5	3
165	Electroluminescence Studies of Modulation p-Doped Quantum Dot Laser Structures. IEEE Journal of Quantum Electronics, 2010, 46, 1847-1853.	1.9	1
166	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Skin Imaging. IEEE Journal of Selected Topics in Quantum Electronics, 2010, 16, 748-754.	2.9	31
167	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Device Engineering. IEEE Journal of Selected Topics in Quantum Electronics, 2010, 16, 1015-1022.	2.9	46
168	Persistent template effect in InAs/GaAs quantum dot bilayers. Journal of Applied Physics, 2010, 107, .	2.5	23
169	Towards 1.55 µm GaAs based lasers using quantum dot bilayers. , 2010, , .		0
170	Simultaneous three-state lasing in quantum dot laser at room temperature. Electronics Letters, 2010, 46, 1155.	1.0	12
171	High performance intermixed p-doped quantum dot superluminescent diodes at 1.2µm. Electronics Letters, 2010, 46, 295.	1.0	15
172	Study of annealed InAs/GaAs quantum dot structures. Journal of Physics: Conference Series, 2010, 209, 012036.	0.4	7
173	Trade-offs in the realization of electrically pumped vertical external cavity surface emitting lasers. , 2010, , .		0
174	Self-assembled quantum-dot superluminescent light-emitting diodes. Advances in Optics and Photonics, 2010, 2, 201.	25.5	93
175	Effects of intermixing on modulation p-doped quantum dot superluminescent light emitting diodes. Optics Express, 2010, 18, 7055.	3.4	22
176	Distributed feedback laser employing buried GaAs/InGaP index-coupled grating. Electronics Letters, 2010, 46, 1076.	1.0	6
177	Gain spectra analysis of bilayer quantum dot lasers beyond 1.3µm. , 2010, , .		0
178	Optical coherence tomography with high power quantum-dot superluminescent diodes. , 2009, , .		0
179	Buried InGaP/GaAs grating distributed feedback laser with AlGaAs cladding. , 2009, , .		0
180	Advanced Wavelength Tunable Quantum Dot Lasers and Broadband Quantum Dot Superluminescent Diodes Obtained by Post-Growth Intermixing. , 2009, , .		0

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181	Analysis of 1.2 μ m InGaAs/GaAs quantum dot laser for high power applications. Journal of Applied Physics, 2009, 106, 073102.	2.5	6
182	A platform for GaAs opto-electronic integrated circuits based on GaAs/AlGaAs overgrowth of patterned InGaP. , 2009, , .		0
183	Operating Characteristics of GaAs/InGaP Self Aligned Stripe Lasers. Japanese Journal of Applied Physics, 2009, 48, 04C120.	1.5	1
184	Evaluation of a cheap ultrasonic stage for light source coherence function measurement, optical coherence tomography, optical coherence microscopy, and dynamic focusing. Proceedings of SPIE, 2009, , .	0.8	0
185	Evaluation of a cheap ultrasonic stage for light source coherence function measurement, optical coherence tomography and dynamic focusing. Measurement Science and Technology, 2009, 20, 107002.	2.6	1
186	Quantum Well and Dot Self-Aligned Stripe Lasers Utilizing an InGaP Optoelectronic Confinement Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 819-827.	2.9	6
187	Tuning Superluminescent Diode Characteristics for Optical Coherence Tomography Systems by Utilizing a Multicontact Device Incorporating Wavelength-Modulated Quantum Dots. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 757-763.	2.9	25
188	Multi-section quantum dot superluminescent diodes for spectral shape engineering. IET Optoelectronics, 2009, 3, 100-104.	3.3	17
189	Low-Dimensional Waveguide Grating Fabrication in GaN with Use of SiCl ₄ /Cl ₂ /Ar-Based Inductively Coupled Plasma Dry Etching. Journal of Electronic Materials, 2009, 38, 635-639.	2.2	16
190	Maximising performance of optical coherence tomography systems using a multi-section chirped quantum dot superluminescent diode. Microelectronics Journal, 2009, 40, 588-591.	2.0	13
191	A p-type-doped quantum dot superluminescent LED with broadband and flat-topped emission spectra obtained by post-growth intermixing under a GaAs proximity cap. Nanotechnology, 2009, 20, 055204.	2.6	23
192	In-Plane Optical Anisotropy of GaN Refractive Index in Visible Light Region. IEEE Photonics Technology Letters, 2009, 21, 966-968.	2.5	10
193	Enhanced room-temperature quantum-dot effects in modulation-doped InAs/GaAs quantum dots. Applied Physics Letters, 2009, 95, 171902.	3.3	18
194	Direct modulation of excited state quantum dot lasers. Applied Physics Letters, 2009, 95, .	3.3	39
195	Broad-band high power quantum dot superluminescent diodes. , 2009, , .		0
196	Multi-contact quantum dot superluminescent diodes for optical coherence tomography. , 2009, , .		0
197	High-Power Quantum-Dot Superluminescent LED With Broadband Drive Current Insensitive Emission Spectra Using a Tapered Active Region. IEEE Photonics Technology Letters, 2008, 20, 782-784.	2.5	27
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